



Thyristor \ Diode Module

 $V_{RRM} = 2x 1200 V$

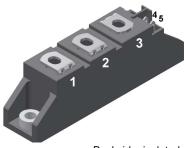
 $I_{TAV} = 35 A$

 $V_{T} = 1.22 V$

Phase leg

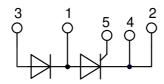
Part number

MCMA35PD1200TB



Backside: isolated





Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

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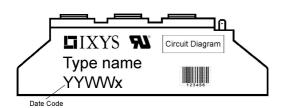


Rectifier					Ratings	>	9
Symbol	Definition	Conditions		min.	typ.	max.	Un
V _{RSM/DSM}	max. non-repetitive reverse/forwa	rd blocking voltage	$T_{VJ} = 25^{\circ}C$			1300	! ! !
V _{RRM/DRM}	max. repetitive reverse/forward ble	ocking voltage	$T_{VJ} = 25^{\circ}C$			1200	i ! !
I _{R/D}	reverse current, drain current	$V_{R/D} = 1200 \text{ V}$	$T_{VJ} = 25^{\circ}C$			100	μ
		$V_{R/D} = 1200 \text{ V}$	$T_{VJ} = 140$ °C			6	m
V _T	forward voltage drop	I _T = 35 A	$T_{VJ} = 25^{\circ}C$			1.23	
		Ι _Τ = 70 A				1.50	! ! !
		$I_{T} = 35 \text{ A}$	$T_{VJ} = 125$ °C			1.22	
		Ι _Τ = 70 A				1.56	
I _{TAV}	average forward current	$T_{c} = 85^{\circ}C$	T _{v.1} = 140°C			35	
I _{T(RMS)}	RMS forward current	180° sine	***			55	! !
V _{T0}	threshold voltage		T _{v.1} = 140°C			0.87	! !
r _T	slope resistance for power lo	ss calculation only	. _V J			9.8	m
R _{thJC}	thermal resistance junction to case	2				0.9	K/V
	thermal resistance junction to case thermal resistance case to heatsir				0.2	0.0	K/V
R _{thCH}		IN.	T _C = 25°C		0.2	120	į
P _{tot}	total power dissipation	4 10 may (50 Hz) sins					V
I _{TSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			520	1
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			560	,
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 140$ °C			440	
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			475	
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			1.35	kA ²
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			1.31	kA ²
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 140$ °C			970	A ²
		t = 8.3 ms; (60 Hz), sine	$V_R = 0 V$			940	A ²
C _J	junction capacitance	$V_R = 400 V$ $f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		22		р
P _{GM}	max. gate power dissipation	t _P = 30 μs	$T_C = 140$ °C			10	٧
		$t_{P} = 300 \mu s$				5	٧
P_{GAV}	average gate power dissipation					0.5	٧
(di/dt) _{cr}	critical rate of rise of current	$T_{v,l} = 140 ^{\circ}\text{C}; f = 50 \text{Hz}$ re	epetitive, $I_T = 105 A$			150	Α/μ
	$t_{\rm p} = 200 \mu \rm s; di_{\rm g}/dt = 0.45 A/\mu \rm s;$						
			on-repet., $I_T = 35 A$			500	A/u
(dv/dt) _{cr}	critical rate of rise of voltage	$V = \frac{2}{3} V_{DBM}$	T _{v.i} = 140°C			1000	i
(at/at/cr		R _{GK} = ∞; method 1 (linear volta	• •				• / [
V _{GT}	gate trigger voltage	$V_D = 6 \text{ V}$	$T_{VJ} = 25^{\circ}C$			1.5	١
V GT	gate ingger venage	v _D = 0 v	$T_{VJ} = -40$ °C			1.6	,
		V 6.V					
I _{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$			78	m
			$T_{VJ} = -40$ °C			200	m/
$V_{\sf GD}$	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^{\circ}C$			0.2	i '
I _{GD}	gate non-trigger current					5	m
I _L	latching current	$t_p = 10 \mu s$	$T_{VJ} = 25^{\circ}C$			450	m
		$I_G = 0.45 A; di_G/dt = 0.45 A/\mu s$					
I _H	holding current	$V_D = 6 V R_{GK} = \infty$	$T_{VJ} = 25$ °C			200	m
t _{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$			2	μ
		$I_G = 0.45 A; di_G/dt = 0.45 A/\mu s$	3				i
tq	turn-off time	$V_R = 100 \text{ V}; I_T = 35\text{A}; V = \frac{2}{3}$	'з V _{DRM} Т _{VJ} =125 °C		185		μ
•		$di/dt = 10 A/\mu s dv/dt = 20 V$	/us t 200 us				İ



MCMA35PD1200TB

Package	Package TO-240AA				Ratings			
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal					80	Α
T _{VJ}	virtual junction temperatur	е			-40		140	°C
T _{op}	operation temperature				-40		125	°C
T _{stg}	storage temperature				-40		125	°C
Weight						81		g
M _D	mounting torque				2.5		4	Nm
$\mathbf{M}_{_{\mathbf{T}}}$	terminal torque				2.5		4	Nm
d _{Spp/App}	oroonogo diatanoo on surf	and Latriking diatance through air	terminal to terminal	13.0	9.7			mm
$d_{Spb/Apb}$	creepage distance on sun	ace striking distance through air	terminal to backside	16.0	16.0			mm
V _{ISOL}	isolation voltage	t = 1 second	50/00 LL 51/0 L	•	4800			٧
1002		t = 1 minute	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA		4000			٧



Part description

M = Module

M = Module
C = Thyristor (SCR)
M = Thyristor
A = (up to 1800V)
35 = Current Rating [A]

PD = Phase leg

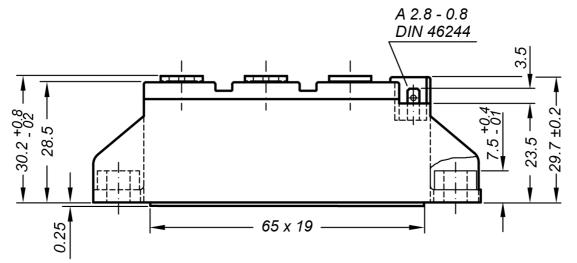
1200 = Reverse Voltage [V] TB = TO-240AA-1B

0	rdering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
St	tandard	MCMA35PD1200TB	MCMA35PD1200TB	Box	36	515940

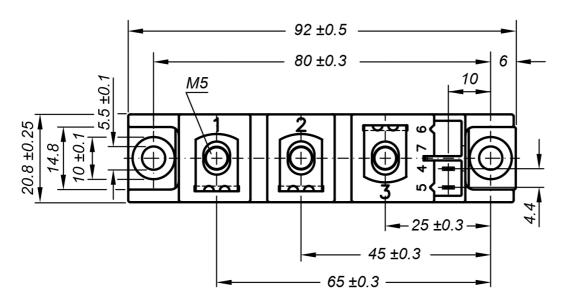
Equiva	lent Circuits for	Simulation	* on die level	$T_{VJ} = 140^{\circ}C$
$I \rightarrow V_0$)—[R _o]-	Thyristor		
V _{0 max}	threshold voltage	0.87		V
$R_{0 max}$	slope resistance *	8.6		$m\Omega$



Outlines TO-240AA

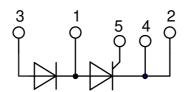


General tolerance: DIN ISO 2768 class "c"



Optional accessories for modules

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red Type ZY 200L (L = Left for pin pair 4/5) UL 758, style 3751







Thyristor

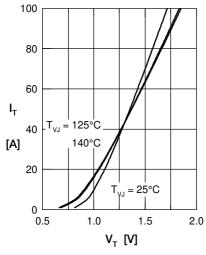


Fig. 1 Forward characteristics

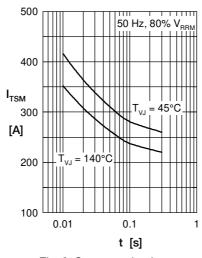


Fig. 2 Surge overload current I_{TSM} : crest value, t: duration

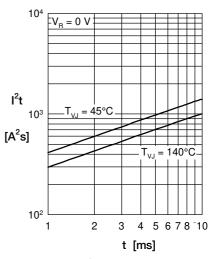


Fig. 3 I²t versus time (1-10 s)

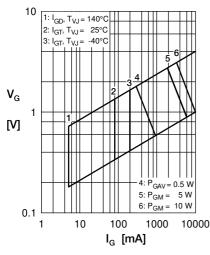


Fig. 4 Gate voltage & gate current

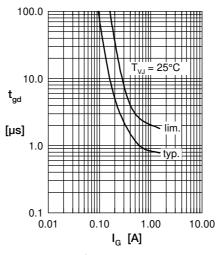


Fig. 5 Gate controlled delay time t_{ad}

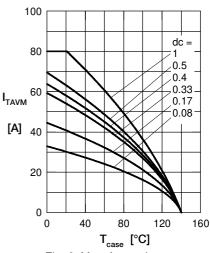


Fig. 6 Max. forward current at case temperature

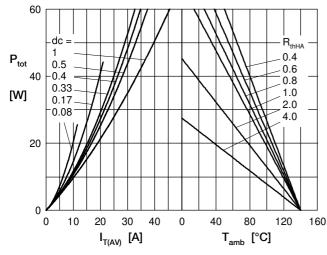


Fig. 7a Power dissipation versus direct output current Fig. 7b and ambient temperature

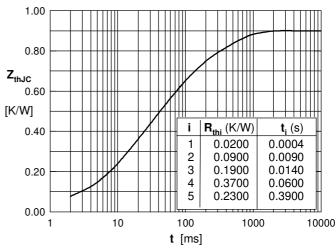


Fig. 8 Transient thermal impedance junction to case

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T360N24TOF T430N16TOF T300N16TOF TD520N22KOF TT305N16KOF TT270N16KOF TD600N16KOF T740N22TOF T640N12TOF
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TD820N16KOFHPSA1 MCD501-16IO2 MCD501-18IO2 SK 100 KQ 12 SK 45 UT 16 SKKT 106B12 E SKKT 27/16E VSST180S12P0VPBF PSET132/16